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CC

PATENT APPLICATION
Docket No: 15436.422.6

EXPRESS MAIL
MAR 28 2005
PATENT & TRADEMARK OFFICE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Bo Su Chen

Serial No.: 10/781,466

Confirmation No.: 1775

Filed: February 17, 2004

For: OPTICAL SYSTEM WITH REDUCED
BACK REFLECTION

Art Unit
2874

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. § 1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Please find, pursuant to 37 C.F.R. § 1.98(a)(1), the enclosed Form PTO-1449 which contains a list of all patents, publications, or other items that have come to the attention of one or more of the individuals designated in 37 C.F.R. § 1.56(c). While no representation is made that any of these references may be "prior art" within the meaning of that term under 35 U.S.C. §§ 102 or 103, the enclosed list of references is disclosed so as to fully comply with the duty of disclosure set forth in 37 C.F.R. § 1.56.

Moreover, while no representation is made that a specific search of office files or patent office records has been conducted or that no better art exists, the undersigned attorney of record

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believes that the enclosed art is the closest to the claimed invention (taken in its entirety) of which the undersigned is presently aware, and no art which is closer to the claimed invention (taken in its entirety) has been knowingly withheld.

In accordance with 37 C.F.R. §§ 1.97 and 1.98, a copy of each of the listed references or relevant portion thereof is also enclosed.

In accordance with 37 C.F.R. § 1.98(c), all English translations within the possession, custody, control or availability of anyone designated in 37 C.F.R. § 1.56(c) of each non-English reference, if any, are also enclosed.

Statement of References Previously Disclosed
Under 37 C.F.R. § 1.98(d)

The following listed references are not enclosed because, under 37 C.F.R. § 1.98(d), they were previously cited by or submitted to the Office in application number 10/610,256 filed June 30, 2003, which is relied upon for an earlier filing date under 35 U.S.C. § 120.

DATED March 28, 2005.

Respectfully submitted,



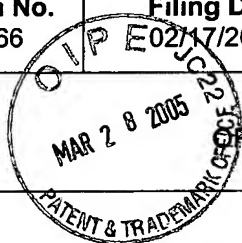
R. Burns Israelsen
Attorney for Applicant
Registration No. 42,685
Customer No. 022913

CERTIFICATE OF MAILING BY "EXPRESS MAIL" (37 CFR 1.10)

Applicant(s): Bo Su Chen

Docket No.
15436.442.6Application No.
10/781,466Filing Date
02/17/2004Examiner
Not Yet AssignedCustomer No
022913Group Art Unit
2874

Invention:



OPTICAL SYSTEM WITH REDUCED BACK REFLECTION

I hereby certify that the following correspondence:

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is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on

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Information Disclosure Statement (2 pages)
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TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**(Under 37 CFR 197(b) or 1.97(c))****Docket No.
15436.442.6****In Re Application Of:**

Bo Su Chen

Application No.

10/781,466

Filing Date

02/17/2004

Examiner

Not Yet Assigned

Customer No

022913

Group Art Unit

2874

Confirmation No.

1775

Title:

OPTICAL SYSTEM WITH REDUCED BACK REFLECTION

Address to:

Commissioner for Patents**P.O. Box 1450****Alexandria, VA 22313-1450****37 CFR 1.97(b)**

1. ☐ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☒ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);

OR

☒ the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
15436.442.6

In Re Application Of:

Bo Su Chen

Application No.
10/781,466Filing Date
02/17/2004Examiner
Not Yet AssignedCustomer No
022913Group Art Unit
2874Confirmation No.
1775

Title:

OPTICAL SYSTEM WITH REDUCED BACK REFLECTION

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of \$ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. 23-3178 as described below.
- ☐ Charge the amount of \$.
- ☒ Credit any overpayment.
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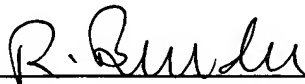
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450" [37 CFR 1.8(a)] on

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Signature of Person Mailing Correspondence

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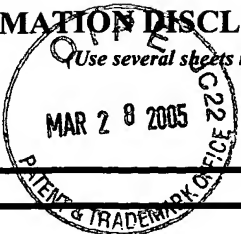
*This certificate may only be used if paying by deposit account.



Signature

Dated: March 28, 2005

cc: R. Burns Israelsen
Attorney for Applicant
Registration No. 42,685

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i> 	Docket number (Optional) 15436.442.6	Application Number 10/781,446
	Applicant(s) Bo Su Chen	
	Filing Date 02/17/2004	Group Art Unit 2874

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,536,959	03/2003	Kuhn, et al.			
		3,271,631	09/1966	J. C. Marinace			
		3,936,742	02/1976	Krause			
		4,408,871	10/1983	Kojima			
		4,490,618	12/1984	Cielo			
		4,678,269	07/1987	Pace			
		4,681,414	07/1987	Hershet			
		4,755,036	07/1988	Suzuki, et al.			
		4,765,703	08/1988	Suzuki, et al.			
		4,816,912	03/1989	Suzuki, et al.			
		4,818,058	04/1995	Bonanni			
		4,829,537	05/1989	Baer			
		4,842,390	06/1989	Sottini, et al.			
		4,894,785	01/1990	Fernandes			
		4,935,029	06/1990	Matsutani, et al.			
		4,943,128	07/1990	Takada, et al.			
		4,976,727	12/1990	Matsutani, et al.			
		5,001,323	03/1991	Matsutani, et al.			
		5,029,101	07/1991	Fernandes			
		5,029,973	07/1991	Rink			
		5,047,076	09/1991	Cagnolato, et al.			
		5,170,406	12/1992	Tidwell			
		5,312,398	05/1994	Hobart, et al.			
		5,354,323	10/1994	Whitebook			
		5,400,145	03/1995	Suita, et al.			
		5,402,258	03/1995	Murakami, et al.			
		5,404,869	04/1995	Parkyn, Jr., et al.			
		5,414,600	05/1995	Strobl, et al.			
		5,415,652	05/1995	Mueller, et al.			
		5,430,634	07/1995	Baker, et al.			
		5,458,594	10/1995	Mueller, et al.			
		5,467,104	11/1995	Burnes, III et al.			
EXAMINER			DATE CONSIDERED				

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION*(Use several sheets if necessary)*

Docket number (Optional)

15436.442.6

Application Number

10/781,446

Applicant(s)

Bo Su Chen

Filing Date

02/17/2004

Group Art Unit

2874

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,470,314	11/1995	Walimsky			
		5,491,344	02/1996	Kenny, et al.			
		5,495,576	02/1996	Ritchey			
		5,509,095	04/1996	Baker, et al.			
		5,530,709	06/1996	Waarts, et al.			
		5,577,492	11/1996	Parkyn, Jr. et al.			
		5,594,752	01/1997	Endriz			
		5,596,339	01/1997	Furness, III et al.			
		5,600,126	02/1997	Appel, et al.			
		5,613,769	03/1997	Parkyn, Jr. et al.			
		5,659,327	08/1997	Furness, III et al.			
		5,676,453	10/1997	Parkyn, Jr. et al.			
		5,677,920	10/1997	Waarts, et al.			
		5,773,817	06/1998	Kingsley, et al.			
		5,777,342	07/1998	Baer			
		5,790,576	08/1998	Waarts, et al.			
		5,793,783	08/1998	Endriz			
		5,799,543	09/1998	Nagai, et al.			
		5,802,092	09/1998	Endriz			
		5,806,955	09/1998	Parkyn, Jr. et al.			
		5,832,055	11/1998	Dewaele			
		5,836,667	11/1998	Baker, et al.			
		5,861,995	01/1999	Gordon			
		5,866,911	02/1999	Baer			
		5,936,777	08/1999	Dempewolf			
		5,952,668	09/1999	Baer			
		5,993,466	11/1999	Yoon			
		5,993,467	11/1999	Yoon			
		5,998,215	12/1999	Prather, et al.			
		6,008,781	12/1999	Furness, III et al.			
		6,075,650	06/2000	Morris, et al.			
		6,139,517	10/2000	Macoviak			

EXAMINER

DATE CONSIDERED

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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,160,916	12/2000	Horiuchi			
		6,186,648	02/2001	Baker, et al.			
		6,222,864	04/2001	Waarts, et al.			
		6,254,563	07/2001	Macoviak, et al.			
		6,259,104	07/2001	Baer			
		6,317,103	11/2001	Furness, III et al.			
		6,324,326	11/2001	Dejneka, et al.			
		6,349,159	02/2002	Uebbing, et al.			
		6,356,572	03/2002	Tanaka, et al.			
		6,366,338	04/2002	Masubuchi, et al.			
		6,410,213	06/2002	Raguin, et al.			
		6,411,835	06/2002	Modell, et al.			
		4,317,085	02/23/1982	Brunham, et al.			
		4,466,694	08/21/1984	MacDonald			
		4,660,207	04/21/1987	Svilans			
		4,675,058	06/23/1987	Plaster			
		4,784,722	11/15/1988	Liau, et al.			
		4,885,592	12/05/1989	Kofol, et al.			
		4,901,327	02/13/1990	Bradley			
		4,943,970	07/24/1990	Bradley			
		4,956,844	09/11/1990	Goodhue, et al.			
		5,031,187	07/09/1991	Orenstein, et al.			
		5,052,016	09/24/1991	Mahbobzadeh			
		5,056,098	10/08/1991	Anthony, et al.			
		5,062,115	10/29/1991	Thornton			
		5,068,869	11/26/1991	Wang, et al.			
		5,079,774	01/07/1992	Mendez, et al.			
		5,115,442	05/19/1992	Lee, et al.			
		5,117,469	05/26/1992	Cheung, et al.			
		5,140,605	08/18/1992	Paoli, et al.			
		5,157,537	10/20/1992	Rosenblatt, et al.			
		5,158,908	10/27/1992	Blonder, et al.			
EXAMINER			DATE CONSIDERED				
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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket number (Optional) 15436.442.6	Application Number 10/781,446
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	Filing Date 02/17/2004	Group Art Unit 2874

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,212,706	05/18/1993	Jain			
		5,216,263	06/01/1993	Paoli			
		5,216,680	06/01/1993	Magnusson, et al.			
		5,237,581	08/17/1993	Asada, et al.			
		5,245,622	09/14/1993	Jewell, et al.			
		5,258,990	11/02/1993	Olbright, et al.			
		5,262,360	11/16/1993	Holonyak, Jr. et al.			
		5,285,466	02/08/1994	Tabatabaie			
		5,293,392	03/08/1994	Shieh, et al.			
		5,317,170	05/31/1994	Paoli			
		5,317,587	05/31/1994	Ackley, et al.			
		5,325,386	06/28/1994	Jewell, et al.			
		5,331,654	07/19/1994	Jewell, et al.			
		5,337,074	08/09/1994	Thornton			
		5,337,183	08/09/1994	Rosenblatt, et al.			
		5,349,599	09/20/1994	Larkins			
		5,351,256	09/27/1994	Schneider, et al.			
		5,359,447	10/25/1994	Hahn, et al.			
		5,359,618	10/25/1994	Lebby, et al.			
		5,363,397	11/08/1994	Collins, et al.			
		5,373,520	12/13/1994	Shoji, et al.			
		5,373,522	12/13/1994	Holonyak, Jr., et al.			
		5,376,580	12/27/1994	Kish, et al.			
		5,386,426	01/31/1995	Stephens			
		5,390,209	02/14/1995	Vakhshoori			
		5,396,508	03/17/1995	Bour, et al.			
		5,404,373	04/04/1995	Cheng			
		5,412,678	05/02/1995	Treat, et al.			
		5,412,680	05/02/1995	Swirham, et al.			
		5,416,044	05/16/1995	Chino, et al.			
		5,428,634	06/27/1995	Bryan, et al.			
		5,438,584	08/01/1995	Paoli, et al.			
EXAMINER			DATE CONSIDERED				

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	Filing Date 02/17/2004	Group Art Unit 2874

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,446,754	08/29/1995	Jewell, et al.			
		5,465,263	11/07/1995	Bour, et al.			
		5,475,701	12/12/1995	Hibbs-Brenner			
		5,493,577	02/1996	Choquette, et al.			
		5,497,390	03/05/1996	Tanaka, et al.			
		5,513,202	04/30/1996	Kobayashi, et al.			
		5,530,715	06/25/1996	Shieh, et al.			
		5,555,255	09/10/1996	Kock, et al.			
		5,557,626	09/17/1996	Grodinski, et al.			
		5,561,683	10/01/1996	Kwon			
		5,567,980	10/22/1996	Holonyak, Jr. et al.			
		5,568,498	10/22/1996	Nilsson			
		5,568,499	10/22/1996	Lear			
		5,574,738	11/12/1996	Morgan			
		5,581,571	12/1996	Holonyak, Jr. et al.			
		5,586,131	12/17/1996	Ono, et al.			
		5,590,145	12/31/1996	Nitta			
		5,598,300	01/28/1997	Magnusson, et al.			
		5,606,572	02/25/1997	Swirhun, et al.			
		5,625,729	04/29/1997	Brown			
		5,642,376	06/24/1997	Olbright, et al.			
		5,645,462	07/08/1997	Banno, et al.			
		5,646,978	07/08/1997	Kem, et al.			
		5,648,978	07/15/1997	Sakata			
		5,679,963	10/21/1997	Klem, et al.			
		5,692,083	11/25/1997	Bennett			
		5,696,023	12/09/1997	Holonyak, Jr., et al.			
		5,699,373	12/16/1997	Uchida, et al.			
		5,712,188	01/27/1998	Chu, et al.			
		5,726,805	03/10/1998	Kaushik, et al.			
		5,727,013	03/10/1998	Botez, et al.			
		5,727,014	03/10/1998	Wang, et al.			
EXAMINER			DATE CONSIDERED				

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	Applicant(s) Bo Su Chen	
	Filing Date 02/17/2004	Group Art Unit 2874

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,774,487	06/30/1998	Morgan			
		5,778,018	07/07/1998	Yoshikawa, et al.			
		5,781,575	07/14/1998	Nilsson			
		5,784,399	07/21/1998	Sun			
		4,790,733	08/04/1998	Smith, et al.			
		5,805,624	09/08/1998	Yang, et al.			
		5,818,066	10/06/1998	Duboz			
		5,828,684	10/27/1998	Van de Walle			
		5,838,705	11/17/1998	Shieh, et al.			
		5,838,715	11/17/1998	Corzine, et al.			
		5,892,784	04/16/1999	Tan, et al.			
		5,892,727	04/06/1999	Tan, et al.			
		5,896,408	04/20/1999	Corzine, et al.			
		5,901,166	05/04/1999	Nitta, et al.			
		5,903,588	05/1999	Guenther, et al.			
		5,903,589	05/1999	Jewell			
		5,903,590	05/11/1999	Hadley, et al.			
		5,908,408	06/1999	McGary, et al.			
		5,936,266	08/10/1999	Holonyak, Jr. et al.			
		5,940,422	08/17/1999	Johnson			
		5,953,362	09/14/1999	Pamulapati, et al.			
		5,978,401	11/02/1999	Morgan			
		5,978,408	11/1999	Thornton			
		5,995,531	11/30/1999	Gaw, et al.			
		6,002,705	12/14/1999	Thornton			
		6,008,675	12/28/1999	Handa			
		6,014,395	01/11/2000	Jewell			
		6,043,104	03/28/2000	Uchida, et al.			
		6,046,065	04/04/2000	Goldstein, et al.			
		6,055,262	04/25/2000	Cox, et al.			
		6,052,398	04/18/2003	Brillouet, et al.			
		6,060,743	05/09/2000	Sugiyama, et al.			
EXAMINER			DATE CONSIDERED				

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	Filing Date 02/17/2004	Group Art Unit 2874

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,078,601	06/20/2000	Smith			
		6,086,263	07/11/200	Selli, et al.			
		6,133,590	10/17/2000	Ashley, et al.			
		6,144,682	11/07/2000	Sun			
		6,154,480	11/28/2000	Magnusson, et al.			
		6,185,241	02/06/2001	Sun			
		6,191,890	02/20/2001	Baets, et al.			
		6,208,681	03/27/2001	Thorton			
		6,212,312	04/03/2001	Grann, et al.			
		6,238,944	05/29/2001	Floyd			
		6,269,109	07/31/2001	Jewell			
		6,297,068	10/02/2001	Thornton			
		6,302,596	10/16/2001	Cohen, et a.			
		6,339,496	01/15/2002	Koley, et al.			
		6,369,403	04/09/2002	Holonyak, Jr.			
		6,372,533	04/16/2002	Jayaraman, et al.			
		6,392,257	05/21/2002	Ramdani, et al.			
		6,410,941	06/25/2002	Taylor, et al.			
		6,411,638	06/25/2002	Johnson, et al.			
		6,427,066	07/30/2002	Grube			
		6,455,879	09/24/2002	Ashley, et al.			
		6,459,709	10/01/2002	Lo, et al.			
		6,459,713	10/01/2002	Jewell			
		6,462,360	10/08/2002	Higgins, Jr. et al.			
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